Product data sheet

1. Product profile

1.1 General description

Silicon Monolithic Microwave Integrated Circuit (MMIC) wideband amplifier with internal matching circuit in a 6-pin SOT363 SMD plastic package.

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features and benefits

- Internally matched to 50 Ω
- Good output match to 75 Ω
- Very high gain; 35.5 dB at 1 GHz
- Upper corner frequency at 2.1 GHz
- 31 dB flat gain up to 2.2 GHz application
- 14 dBm saturated output power at 1 GHz
- High linearity (23 dBm IP3_{out} and 43 dBc IM2)
- 40 dB isolation.

1.3 Applications

- Low Noise Block (LNB) Intermediate Frequency (IF) amplifiers
- Cable systems
- General purpose.

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_S	DC supply voltage	RF input; AC coupled	-	5	6	V
Is	DC supply current		23	27.5	33	mA
$ s_{21} ^2$	insertion power gain	f = 1 GHz	34.5	35.5	36.2	dB
NF	noise figure	f = 1 GHz	-	4.6	4.7	dB
P _{L(sat)}	saturated load power	f = 1 GHz	13.0	14.0	-	dBm



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2. Pinning information

Table 2. Pinning

I do L	9		
Pin	Description	Simplified outline	Symbol
1	V_S	∏6 ∏5 ∏4	,
2, 5	GND2		1
3	RF_OUT		
4	GND1		6 3
6	RF_IN		4 2, 5
			sym062

3. Ordering information

Table 3. Ordering information

Type number	Package	Package					
	Name	Description	Version				
BGM1013	SC-88	plastic surface mounted package; 6 leads	SOT363				

4. Marking

Table 4. Marking codes

Type number	Marking code
BGM1013	C4-

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_S	DC supply voltage	RF input; AC coupled	-	6	V
Is	DC supply current		-	35	mA
P _{tot}	total power dissipation	T _{sp} ≤ 90 °C	-	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
P_{D}	maximum drive power		-	-10	dBm

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6. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Vs	supply voltage		4.5	5.0	5.5	V
T _{amb}	ambient temperature		-40	25	85	°C

7. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	P_{tot} = 200 mW; $T_{sp} \le 90$ °C	300	K/W

8. Characteristics

Table 8. Characteristics

 $V_S = 5 \text{ V; } I_S = 27.5 \text{ mA; } T_i = 25 \text{ °C; measured on demo board; unless otherwise specified.}$

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Vs	DC supply voltage	RF input; AC coupled	-	5	6	V
Is	DC supply current		23	27.5	33	mΑ
$ s_{21} ^2$	insertion power gain	f = 100 MHz	34.5	35.2	35.9	dB
		f = 1 GHz	34.5	35.5	36.2	dB
		f = 1.8 GHz	33.0	34.0	35.2	dB
		f = 2.2 GHz	30.5	31.8	33.1	dB
		f = 2.6 GHz	25.2	29.7	31.2	dB
		f = 3 GHz	24.0	26.1	27.9	dB
$ s_{11} ^2$	input return loss	f = 1 GHz	10.1	10.6	-	dB
		f = 2.2 GHz	9.3	10.2	-	dB
$ s_{22} ^2$	output return loss	$Z_L = 50 \Omega$				
		f = 1 GHz	18	20	-	dB
		f = 2.2 GHz	13	16	-	dB
		$Z_L = 75 \Omega$				
		f = 1 GHz	15	17	-	dB
		f = 2.2 GHz	12	15	-	dB
$ s_{12} ^2$	isolation	f = 1 GHz	40	42	-	dB
		f = 2.2 GHz	34	36	-	dB
NF	noise figure	f = 1 GHz	-	4.6	4.7	dB
		f = 2.2 GHz	-	4.9	5.1	dB
В	bandwidth	3 dB below flat gain at f = 1 GHz	-	2.1	-	GHz
K	stability factor	f = 1 GHz	1.2	1.3	-	
		f = 2.2 GHz	0.9	1.0	-	
P _{L(sat)}	saturated load power	f = 1 GHz	13.0	14.0	-	dBm
		f = 2.2 GHz	9.0	10.2	-	dBm

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 Table 8.
 Characteristics ...continued

 $V_S = 5 \text{ V}$; $I_S = 27.5 \text{ mA}$; $T_i = 25 ^{\circ}\text{C}$; measured on demo board; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
P _{L(1dB)}	load power at 1 dB gain	f = 1 GHz	12.0	13.0	-	dBm
	compression	f = 2.2 GHz	7.0	8.1	-	dBm
IP3 _{in}	input third order intercept point	f = 1 GHz	-14	-12.8	-	dBm
		f = 2.2 GHz	-15	-13.2	-	dBm
IP3 _{out}	output third order intercept point	f = 1 GHz	21	22.7	-	dBm
		f = 2.2 GHz	17	18.6	-	dBm
IM2	second order intermodulation product	$f_0 = 1 \text{ GHz}; P_D = -45 \text{ dBm } (P_L = -10 \text{ dBm})$	-	45	43	dBc
		$f_0 = 1 \text{ GHz}; P_D = -40 \text{ dBm } (P_L = -5 \text{ dBm})$	-	43	41	dBc

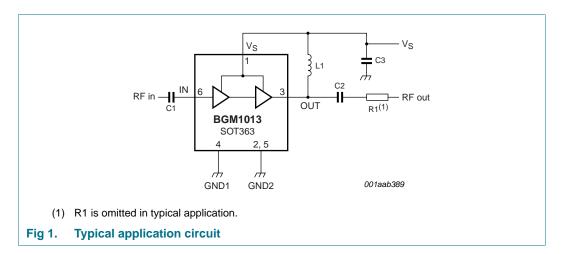
9. Application information

<u>Figure 1</u> shows a typical application circuit for the BGM1013 MMIC. The device is internally matched to 50 Ω and therefore does not need any external matching. Output impedance is also very good to 75 Ω load. The value of the input and output DC blocking capacitors C1 and C2 should be not more than 100 pF for applications above 100 MHz. Their values can be used to fine-tune the input and output impedance.

For the RF-choke, optimal results are obtained with a good quality chip inductor like the TDK MLG1608 (0603) or a wire-wound SMD. The value of the inductor can be used to fine-tune the output impedance.

The RF choke and supply decoupling components should be located as close as possible to the MMIC.

Ground paths must be as short as possible. The printed-circuit board (PCB) top ground plane must be as close as possible to the MMIC, and ideally directly beneath it. When using vias, use at least 3 vias for the top ground plane in order to limit ground path inductance. Supply decoupling with C3 should be from pin 1 to the same top ground plane.



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Figure 2 shows the PCB layout used for the typical application.

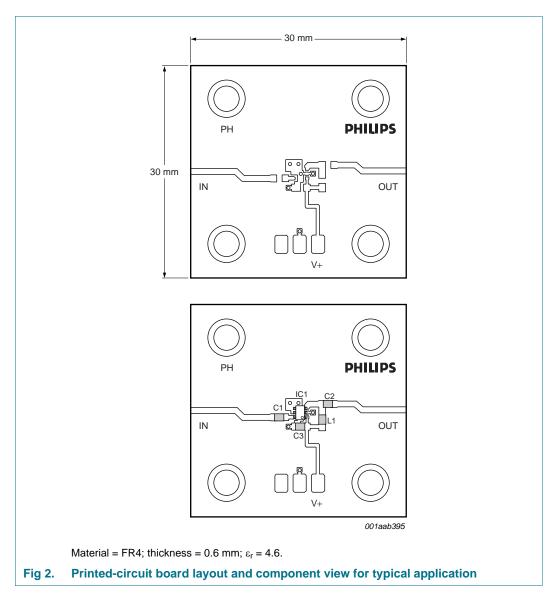


Table 9. List of components used for the typical application

ultilayer ceramic chip capacitor	100 pF	0603
ultilayer ceramic chip capacitor	22 nF	0603
MD resistor	-	0603
MD inductor	100 nH	0603
u	Itilayer ceramic chip capacitor ID resistor	Itilayer ceramic chip capacitor 22 nF ID resistor -

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9.1 Flat gain application: 31 dB between 800 MHz and 2.2 GHz

By changing the components at the output of the amplifier, a flatter gain can be obtained. The gain is 31 dB \pm 1 dB between 800 MHz and 2.2 GHz. $P_{L(1dB)}$ is 10 dBm at 1 GHz and 5.7 dBm at 2.2 GHz.

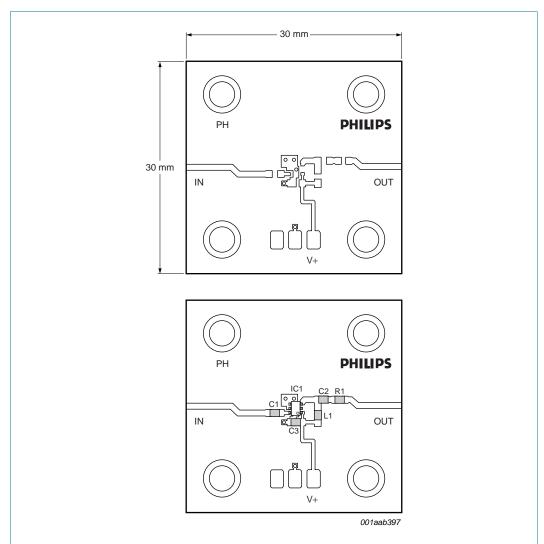


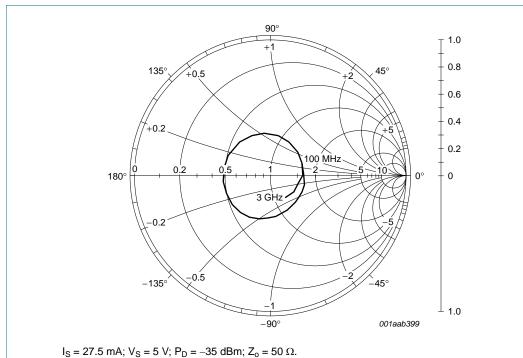
Fig 3. Printed-circuit board layout and component view for 31 dB flat gain application

Table 10. List of components used for the 31 dB flat gain application[1]

Description	Value	Dimensions
multilayer ceramic chip capacitor	100 pF	0603
multilayer ceramic chip capacitor	4.7 pF	0603
multilayer ceramic chip capacitor	22 nF	0603
SMD resistor	27 Ω	0603
SMD inductor	5.6 nH	0603
	multilayer ceramic chip capacitor multilayer ceramic chip capacitor multilayer ceramic chip capacitor SMD resistor	multilayer ceramic chip capacitor 100 pF multilayer ceramic chip capacitor 4.7 pF multilayer ceramic chip capacitor 22 nF SMD resistor 27 Ω

^[1] Pin 2 should not be connected in order to obtain optimal input matching.

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 $1S = 27.5 \text{ mA}, VS = 5 \text{ V}, VD = -35 \text{ dBm}, Z_0 = 50.52.$

Fig 4. Input reflection coefficient (s₁₁); typical values

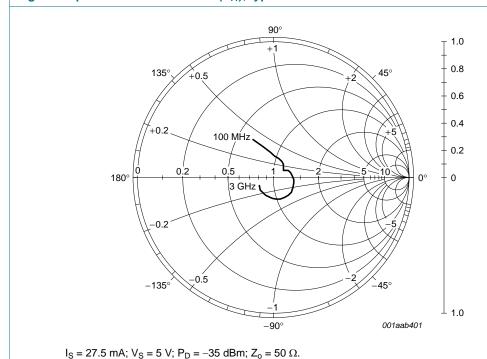
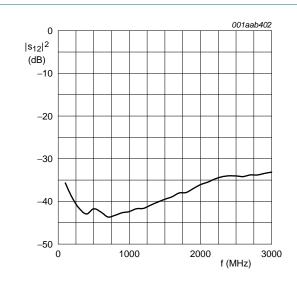


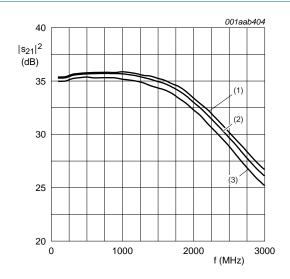
Fig 5. Output reflection coefficient (s₂₂); typical values

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 I_S = 27.5 mA; V_S = 5 V; P_D = –35 dBm; Z_o = 50 $\Omega.$



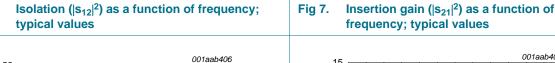
 $P_D = -35 \text{ dBm}; Z_0 = 50 \Omega.$

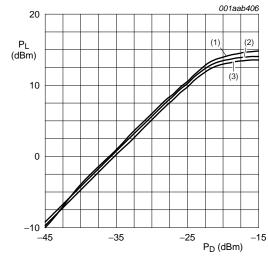
(1) $I_S = 32.6 \text{ mA}$; $V_S = 5.5 \text{ V}$.

(2) $I_S = 27.5 \text{ mA}$; $V_S = 5 \text{ V}$.

(3) $I_S = 21.5 \text{ mA}$; $V_S = 4.5 \text{ V}$.

Isolation ($|s_{12}|^2$) as a function of frequency; Fig 6.





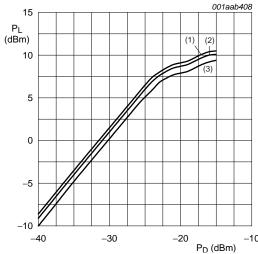
f = 1 GHz; $Z_0 = 50 \Omega$.

(1) $V_S = 5.5 \text{ V}.$

(2) $V_S = 5 V$.

(3) $V_S = 4.5 V.$

Fig 8. Load power as a function of drive power at 1 GHz; typical values



f = 2.2 GHz; $Z_0 = 50 Ω$.

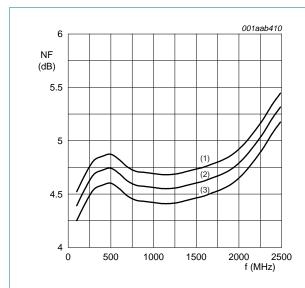
(1) $V_S = 5.5 \text{ V}.$

(2) $V_S = 5 V$.

(3) $V_S = 4.5 V.$

Load power as a function of drive power at Fig 9. 2.2 GHz; typical values

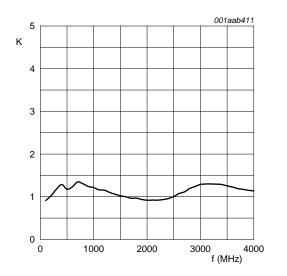
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 $Z_o = 50 \Omega$.

- (1) $V_S = 5.5 V$.
- (2) $V_S = 5 V$.
- (3) $V_S = 4.5 V.$

Fig 10. Noise figure as a function of frequency; typical values



 I_S = 27.5 mA; V_S = 5 V; Z_o = 50 $\Omega.$

Fig 11. Stability factor as a function of frequency; typical values

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Table 11. Scattering parameters $V_S = 5 \ V; \ I_S = 27.5 \ mA; \ P_D = -35 \ dBm; \ Z_o = 50 \ \Omega; \ T_{amb} = 25 \ ^{\circ}C; \ measured on demo board.$

f (MHz)	s ₁₁		s ₂₁	s ₂₁		s ₁₂			K-factor
	Magnitude (ratio)	Angle (deg)	Magnitude (ratio)	Angle (deg)	Magnitude (ratio)	Angle (deg)	Magnitude (ratio)	Angle (deg)	
100	0.259	19.3	57.79	2.5	0.01642	47.3	0.325	118.6	0.9
200	0.258	3.2	57.96	-10.9	0.01096	20.7	0.248	110.9	1.0
400	0.270	-25.6	60.08	-41.2	0.00712	-12.6	0.163	87.0	1.3
600	0.271	-43.7	60.60	-67.0	0.00751	-13.9	0.134	63.2	1.2
800	0.281	-61.5	60.74	-95.6	0.00687	-12.1	0.104	43.7	1.3
1000	0.296	-80.1	60.44	-121.2	0.00759	-7.3	0.092	37.7	1.2
1200	0.317	-102.3	59.21	-147.1	0.00828	-11.5	0.097	33.9	1.2
1400	0.335	-127.7	57.01	-172.9	0.00981	-16.8	0.123	25.6	1.1
1600	0.334	-158.1	54.46	160.8	0.01130	-25.1	0.142	6.0	1.0
1800	0.331	169.6	50.31	134.1	0.01272	-34.0	0.157	-14.2	1.0
2000	0.326	130.6	44.63	104.7	0.01571	-43.0	0.172	-39.8	0.9
2200	0.309	95.9	38.92	79.4	0.01826	-57.0	0.172	-61.9	0.9
2400	0.287	59.0	33.31	55.5	0.01994	-69.2	0.161	-83.5	1.0
2600	0.257	20.4	28.20	33.1	0.01952	-78.3	0.147	-104.4	1.1
2800	0.224	-15.5	23.60	13.1	0.02037	-89.9	0.139	-125.1	1.2
3000	0.198	-50.7	20.24	-4.8	0.02198	-99.8	0.127	-151.5	1.3

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10. Package outline

Plastic surface-mounted package; 6 leads

SOT363

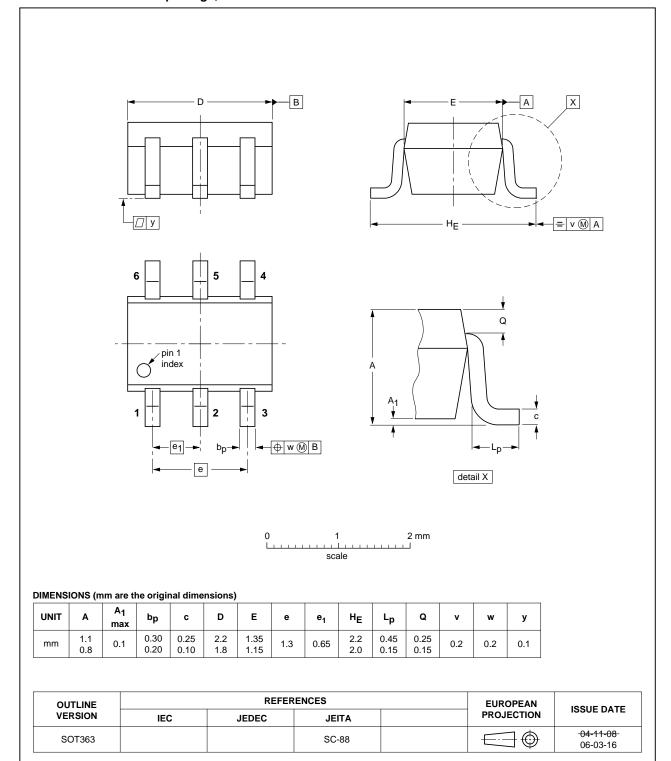


Fig 12. Package outline SOT363 (SC-88)

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11. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGM1013 v.5	20110919	Product data sheet	-	BGM1013 v.4
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 			
	 Legal texts h 	ave been adapted to the new	company name whe	re appropriate.
BGM1013 v.4	20060501	Product data sheet	-	BGM1013 v.3
BGM1013 v.3 (9397 750 14413)	20041209	Product data sheet	-	BGM1013 v.2
BGM1013 v.2 (9397 750 14229)	20041130	Product data sheet	-	BGM1013 v.1
BGM1013 v.1 (9397 750 13469)	20040831	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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